

## Excellent Integrated System Limited

Stocking Distributor

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[IXYS Corporation](#)  
[DPG30C200PB](#)

For any questions, you can email us directly:  
[sales@integrated-circuit.com](mailto:sales@integrated-circuit.com)



**DPG30C200PB**

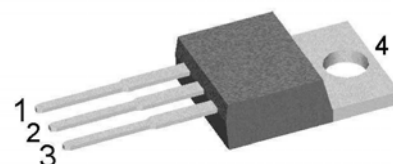
## HiPerFRED<sup>2</sup>

$V_{RRM} = 200V$   
 $I_{FAV} = 2x \ 15A$   
 $t_{rr} = 35ns$

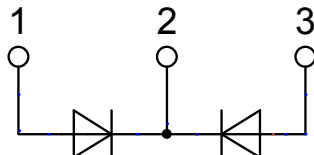
High Performance Fast Recovery Diode  
 Low Loss and Soft Recovery  
 Common Cathode

Part number

**DPG30C200PB**



Backside: cathode



### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

### Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

### Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

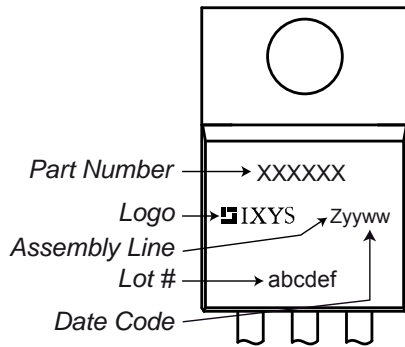
Fast Diode				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage				200	V
$V_{RRM}$	max. repetitive reverse blocking voltage				200	V
$I_R$	reverse current, drain current	$V_R = 200\text{ V}$	$T_{VJ} = 25^\circ\text{C}$		1	$\mu\text{A}$
		$V_R = 200\text{ V}$	$T_{VJ} = 150^\circ\text{C}$		0.08	mA
$V_F$	forward voltage drop	$I_F = 15\text{ A}$	$T_{VJ} = 25^\circ\text{C}$		1.26	V
					1.51	V
		$I_F = 30\text{ A}$	$T_{VJ} = 150^\circ\text{C}$		1.01	V
					1.29	V
$I_{FAV}$	average forward current	$T_C = 145^\circ\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^\circ\text{C}$		15	A
$V_{F0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^\circ\text{C}$		0.69	V
$r_F$	slope resistance				18	m $\Omega$
$R_{thJC}$	thermal resistance junction to case				1.7	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.50		K/W
$P_{tot}$	total power dissipation		$T_C = 25^\circ\text{C}$		90	W
$I_{FSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^\circ\text{C}$		240	A
$C_J$	junction capacitance	$V_R = 150\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		20	pF
$I_{RM}$	max. reverse recovery current	} $I_F = 15\text{ A}; V_R = 130\text{ V}$ $-di_F/dt = 200\text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$		3	A
$t_{rr}$	reverse recovery time		$T_{VJ} = 125^\circ\text{C}$		6.5	A
			$T_{VJ} = 25^\circ\text{C}$		35	ns
			$T_{VJ} = 125^\circ\text{C}$		55	ns



# DPG30C200PB

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal <sup>1)</sup>			35	A
$T_{VJ}$	virtual junction temperature		-55		175	°C
$T_{op}$	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				2		g
$M_D$	mounting torque		0.4		0.6	Nm
$F_C$	mounting force with clip		20		60	N

### Product Marking



### Part number

- D = Diode
- P = HiPerFRED
- G = extreme fast
- 30 = Current Rating [A]
- C = Common Cathode
- 200 = Reverse Voltage [V]
- PB = TO-220AB (3)

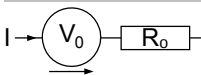
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG30C200PB	DPG30C200PB	Tube	50	505804

Similar Part	Package	Voltage class
DPG30C200PC	TO-263AB (D2Pak) (2)	200
DPG30C200HB	TO-247AD (3)	200

### Equivalent Circuits for Simulation

\* on die level

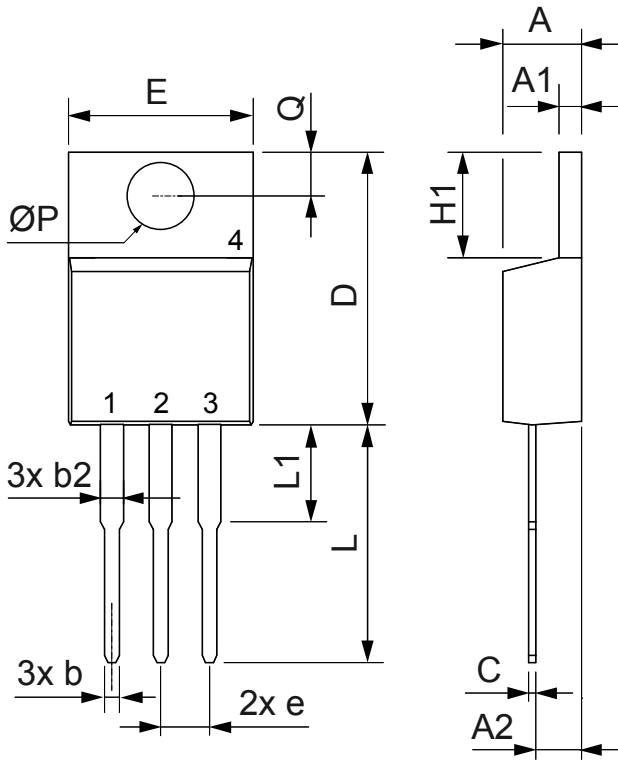
$T_{VJ} = 175\text{ °C}$



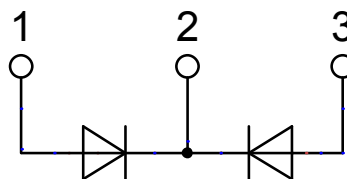
**Fast Diode**

$V_{0\ max}$	threshold voltage	0.69	V
$R_{0\ max}$	slope resistance *	14.7	mΩ

Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



**Fast Diode**

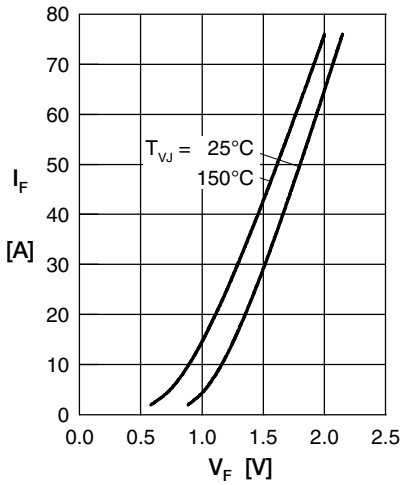


Fig. 1 Forward current  $I_F$  versus  $V_F$

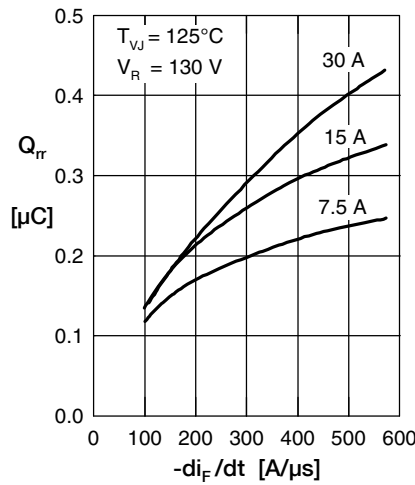


Fig. 2 Typ. reverse recov. charge  $Q_{rr}$  versus  $-di_F/dt$

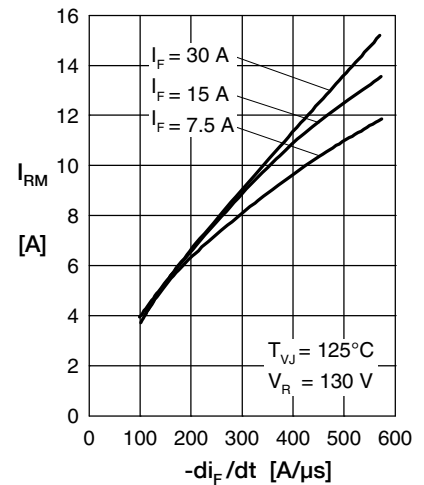


Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$

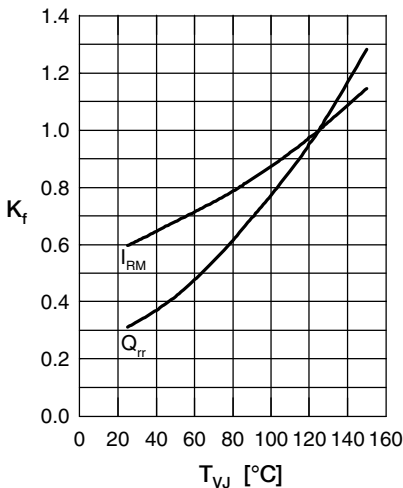


Fig. 4 Typ. dynamic parameters  $Q_{rr}$ ,  $I_{RM}$  versus  $T_{VJ}$

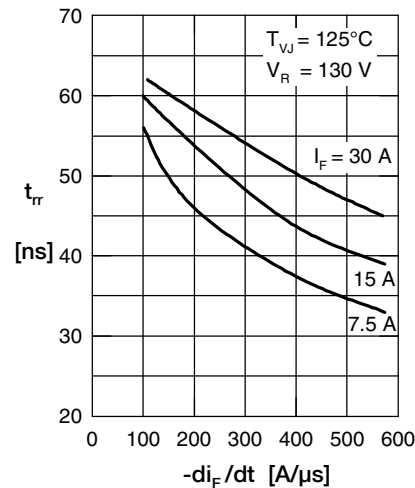


Fig. 5 Typ. recovery time  $t_{tr}$  versus  $-di_F/dt$

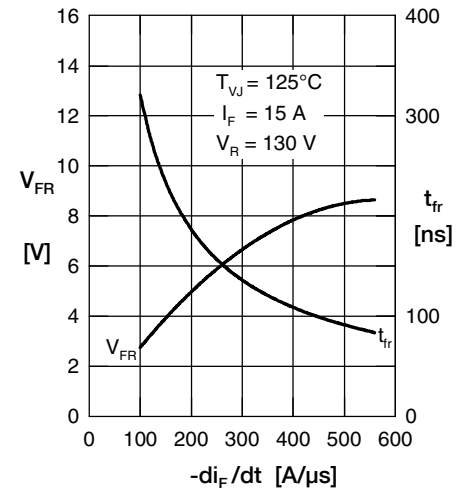


Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{tr}$  versus  $di_F/dt$

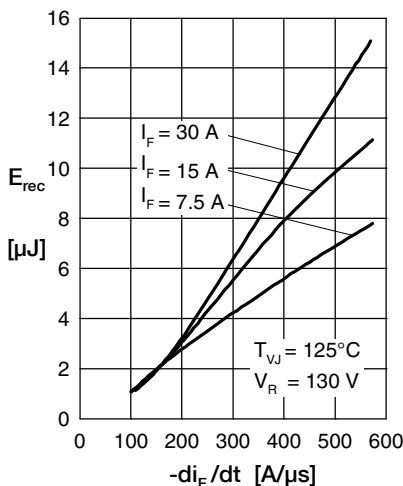


Fig. 7 Typ. recovery energy  $E_{rec}$  versus  $-di_F/dt$

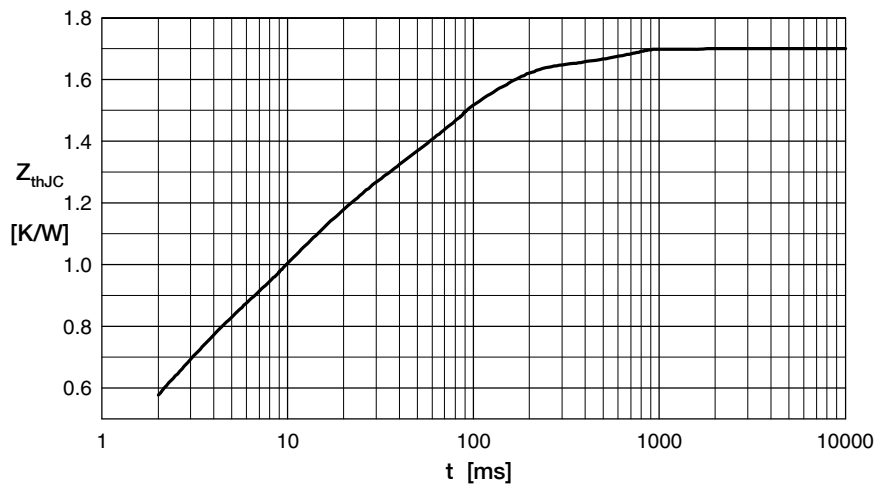


Fig. 8 Transient thermal resistance junction to case